# **OPE5294**

The **OPE5294** is GaAs infrared emitting diode that is designed for low forward voltage and high reliability. This device is optimized for efficiency at emission wavelength 940nm and has a high radiant efficiency over a wide range of forward current. This device is packaged T1-3/4 plastic package and has wide beam angle with lensed package and cup frame.

## **FEATURES**

- High-output power
- Wide beam angle
- High reliability
- Available for pulse operating
- Low cost

# **APPLICATIONS**

- Optical emitters
- Optical switches
- Smoke sensors
- IR remote control
- IR sound transmission

# 2-\(\text{0.5}\) 2.0 2.5

DIMENSIONS (Unit: mm)

Tolerance: ±0.2mm

Anode

Cathode

## **STORAGE**

• Condition: 5°C~35°C,R.H.60%

• Terms: within 3 months from production date

• Remark : Once the package is opened, the products should be used within a day. Otherwise, it should be keeping in a damp proof box with desiccants.

\* Please take proper steps in order to secure reliability and safety in required conditions and environments for this device.

## **MAXIMUM RATINGS**

(Ta=25°C)

Item	Symbol	Rating	Unit	
Power Dissipation	$P_{\mathrm{D}}$	150	mW	
Forward current	$I_{\mathrm{F}}$	100	mA	
Pulse forward current *1	$I_{FP}$	1.0	A	
Reverse voltage	$V_R$	5.0	V	
Operating temp.	Topr.	<b>-</b> 25∼ +85	°C	
Soldering temp. *2	Tsol.	260.	°C	

 $<sup>^{*1}</sup>$ .Duty ratio = 1/100, pulse width=0.1ms.

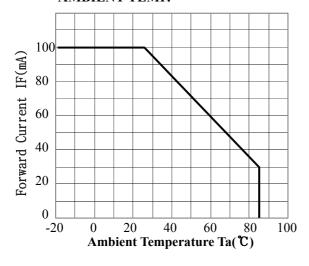
# **ELECTRO-OPTICALCHARACTERISTICS**

 $(Ta=25^{\circ}C)$ 

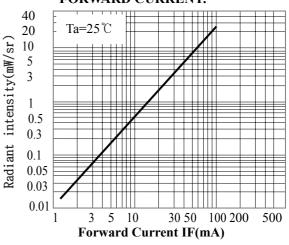
Item	Symbol	Conditions	Min.	Тур.	Max.	Unit
Forward voltage	$V_{\mathrm{F}}$	$I_F = 100 \text{mA}$		1.4	1.7	V
Reverse current	$I_R$	$V_R = 5V$			10	μΑ
Capacitance	Ct	f = 1 MHz		20		pF
Radiant intensity	Ie	$I_F=100mA$		30		mW/sr
Peak emission wavelength	$\lambda_p$	$I_F = 50 \text{mA}$		940		nm
Spectral bandwidth 50%	Δλ	$I_F = 50 \text{mA}$		45		nm
Half angle	ΔΘ	I <sub>F</sub> =100mA		±22		deg.

<sup>\*2.</sup>Lead Soldering Temperature (2mm from case for 5sec.).

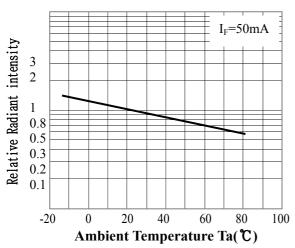
• FORWARD CURRENT Vs. AMBIENT TEMP.



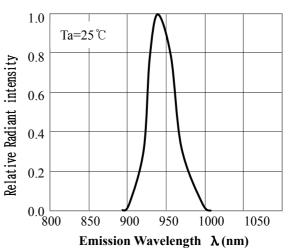
 RADIANT INTENSITY Vs. FORWARD CURRENT.



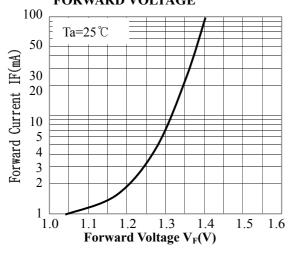
• RELATIVE RADIANT INTENSITY Vs. AMBIENT TEMP.



• RELATIVE RADIANT INTENSITY Vs. EMISSION WAVELENGTH.



• FORWARD CURRENT Vs. FORWARD VOLTAGE



• ANGULAR DISPLACEMENT Vs RELATIVE RADIANT INTENSITY

